

Chun-Hsing Shih

List of Publications by Year in descending order

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#	ARTICLE	IF	CITATIONS
1	Sub-10-nm Tunnel Field-Effect Transistor With Graded Si/Ge Heterojunction. IEEE Electron Device Letters, 2011, 32, 1498-1500.	3.9	76
2	Design and Modeling of Line-Tunneling Field-Effect Transistors Using Low-Bandgap Semiconductors. IEEE Transactions on Electron Devices, 2014, 61, 1907-1913.	3.0	24
3	Nonvolatile Schottky Barrier Multibit Cell With Source-Side Injected Programming and Reverse Drain-Side Hole Erasing. IEEE Transactions on Electron Devices, 2010, 57, 1774-1780.	3.0	20
4	Schottky Barrier Silicon Nanowire SONOS Memory With Ultralow Programming and Erasing Voltages. IEEE Electron Device Letters, 2011, 32, 1477-1479.	3.9	17
5	Multilevel Schottky Barrier Nanowire SONOS Memory With Ambipolar n- and p-Channel Cells. IEEE Transactions on Electron Devices, 2012, 59, 1614-1620.	3.0	17
6	Oxide thickness-dependent effects of source doping profile on the performance of single- and double-gate tunnel field-effect transistors. Superlattices and Microstructures, 2017, 102, 284-299.	3.1	17
7	A Source-Side Injection Lucky Electron Model for Schottky Barrier Metal-Oxide-Semiconductor Devices. IEEE Electron Device Letters, 2011, 32, 1331-1333.	3.9	16
8	Thin Film Applications in Advanced Electron Devices. Advances in Materials Science and Engineering, 2014, 2014, 1-2.	1.8	15
9	Source-side injection Schottky barrier flash memory cells. Semiconductor Science and Technology, 2009, 24, 025013.	2.0	14
10	Short-channel effect and device design of extremely scaled tunnel field-effect transistors. Microelectronics Reliability, 2015, 55, 31-37.	1.7	14
11	Coupling of carriers injection and charges distribution in Schottky barrier charge-trapping memories using source-side electrons programming. Semiconductor Science and Technology, 2014, 29, 115006.	2.0	12
12	Short channel effects in tunnel field-effect transistors with different configurations of abrupt and graded Si/SiGe heterojunctions. Superlattices and Microstructures, 2016, 100, 857-866.	3.1	12
13	Sub-10-nm Asymmetric Junctionless Tunnel Field-Effect Transistors. IEEE Journal of the Electron Devices Society, 2014, 2, 128-132.	2.1	11
14	Reading Operation and Cell Scalability of Nonvolatile Schottky barrier Multibit Charge-Trapping Memory Cells. IEEE Transactions on Electron Devices, 2012, 59, 1599-1606.	3.0	9
15	Device physics and design of hetero-gate dielectric tunnel field-effect transistors with different low/high-k EOT ratios. Applied Physics A: Materials Science and Processing, 2020, 126, 1.	2.3	6
16	A Localized Two-Bit/Cell Nanowire SONOS Memory Using Schottky Barrier Source-Side Injected Programming. IEEE Nanotechnology Magazine, 2013, 12, 760-765.	2.0	5
17	Proper determination of tunnel model parameters for indirect band-to-band tunneling in compressively strained Si _{1-x} Ge _x TFETs. , 2013, , .		5
18	Device physics and design of symmetrically doped tunnel field-effect transistors. Microelectron Engineering, 2019, 216, 111061.	2.4	4

#	ARTICLE	IF	CITATIONS
19	Effects of Dopant-Segregated Profiles on Schottky Barrier Charge-Trapping Flash Memories. IEEE Transactions on Electron Devices, 2014, 61, 1361-1368.	3.0	3
20	Different scalabilities of N- and P-type tunnel field-effect transistors with Si/SiGe heterojunctions. , 2016, , .		3
21	Increasing drain voltage of low-bandgap tunnel field-effect transistors by drain engineering. , 2016, , .		3
22	Bandgap-dependent onset behavior of output characteristics in line-tunneling field-effect transistors. Journal of Computational Electronics, 2017, 16, 696-703.	2.5	3
23	Dependence of Short-Channel Effects on Semiconductor Bandgap in Tunnel Field-Effect Transistors. Journal of Physics: Conference Series, 2018, 1034, 012003.	0.4	3
24	Quantum confinement effect in strained-SiSiGe double-gate tunnel field-effect transistors. , 2013, , .		2
25	Fringing field and short channel effects in thin-body SOI MOSFETs with shallow source/drain. , 2013, , .		2
26	Metallic Schottky barrier source/drain nanowire transistors using low-temperature microwave annealed nickel, ytterbium, and titanium silicidation. Materials Science in Semiconductor Processing, 2017, 70, 272-278.	4.0	2
27	On-current limitation of high-k gate insulator MOSFETs. , 2011, , .		1
28	Sub-10V 4-bit/cell Schottky barrier nanowire nonvolatile memory. , 2012, , .		1
29	Impact of gate-to-source/drain misalignments on source-side injection Schottky barrier charge-trapping memory cells evaluated using numerical programming-trapping iterations. Microelectronics Reliability, 2017, 74, 9-14.	1.7	1
30	Effects of High Temperatures on Cell Reading, Programming, and Erasing of Schottky Barrier Charge-Trapping Memories. IEEE Transactions on Device and Materials Reliability, 2019, 19, 426-432.	2.0	1
31	Influence of hetero-gate dielectrics on short-channel effects in scaled tunnel field-effect transistors. Current Applied Physics, 2020, 20, 1342-1350.	2.4	1
32	Transverse Scaling of Schottky Barrier Charge-Trapping Cells for Energy-Efficient Applications. Crystals, 2020, 10, 1036.	2.2	1
33	Device operation and physical mechanism of asymmetric junctionless tunnel field-effect transistors designed to suppress coupled short-channel/short-drain effects and promote on-current switching for ultralow-voltage CMOS applications. Semiconductor Science and Technology, 2022, 37, 065007.	2.0	1
34	Ambipolar conduction in recessed channel Schottky barrier MOSFETs. , 2010, , .		0
35	Efficient and reliable Schottky barrier silicon nanowire charge-trapping flash memory. , 2012, , .		0
36	P-channel Schottky barrier nanowire SONOS memory with low-voltage operations and excellent reliability. , 2012, , .		0

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37	Formation of arsenic segregated Ytterbium and Nickel silicide using microwave annealing. , 2013, , .		0
38	Drain-controlled ambipolar conduction and hot-hole injection in Schottky barrier charge-trapping memory cells. , 2015, , .		0
39	Iterative programming analysis of dopant-segregated multibit/cell Schottky barrier charge-trapping memories. , 2015, , .		0
40	Dopant-segregated metal source tunnel field-effect transistors with schottky barrier and band-to-band tunneling. , 2017, , .		0
41	Metallic Source/Drain Ge-Based Charge-Trapping Memory Cells. , 2019, , .		0
42	Negative Capacitance in Short-Channel Tunnel Field-Effect Transistors. , 2019, , .		0